

# CITATION REPORT

List of articles citing

## InGaN Light-Emitting Diodes on c-Face Sapphire Substrates in Green Gap Spectral Range

DOI: 10.7567/apex.6.111004  
Applied Physics Express, 2013, 6, 111004.

**Source:** <https://exaly.com/paper-pdf/55043229/citation-report.pdf>

**Version:** 2024-04-26

This report has been generated based on the citations recorded by exaly.com for the above article. For the latest version of this publication list, visit the link given above.

The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

#	Paper	IF	Citations
138	Detailed optical and electrical characterisation of green Orange InGaN/GaN LEDs grown by MOVPE. <b>2014</b> ,		
137	Enhancing the quantum efficiency of InGaN yellow-green light-emitting diodes by growth interruption. <i>Applied Physics Letters</i> , <b>2014</b> , 105, 071108	3.4	33
136	Monolithic white light emitting diodes using a (Ga,In)N-based light converter. <b>2014</b> ,		1
135	The properties of reversed polarization yellow InGaN-GaN MQWs in p-side down structure grown by metalorganic chemical vapor deposition on sapphire substrate. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , <b>2014</b> , 64, 57-62	3	4
134	Realization of high-luminous-efficiency InGaN light-emitting diodes in the "green gap" range. <b>2015</b> , 5, 10883		81
133	Effect of localization states on the electroluminescence spectral width of bluegreen light emitting InGaN/GaN multiple quantum wells. <b>2015</b> , 33, 061502		13
132	Internal quantum efficiency in yellow-amber light emitting AlGaIn-InGaIn-GaN heterostructures. <i>Applied Physics Letters</i> , <b>2015</b> , 107, 122103	3.4	30
131	Effect of the design of the active region of monolithic multi-color LED heterostructures on their spectra and emission efficiency. <b>2015</b> , 49, 1516-1521		2
130	Thermally Engineered Flip-Chip InGaIn/GaN Well-Ordered Nanocolumn Array LEDs. <b>2015</b> , 27, 2343-2346		5
129	On the increased efficiency in InGaIn-based multiple quantum wells emitting at 530-590 nm with AlGaIn interlayers. <b>2015</b> , 415, 57-64		39
128	Optimal ways of colour mixing for high-quality white-light LED sources. <b>2015</b> , 212, 914-919		31
127	Advantages of III-nitride laser diodes in solid-state lighting. <b>2015</b> , 212, 980-985		53
126	Photoluminescence behavior of amber light emitting GaInN-GaN heterostructures. <b>2015</b> ,		
125	Strain-compensated (Ga,In)N/(Al,Ga)N/GaN multiple quantum wells for improved yellow/amber light emission. <i>Applied Physics Letters</i> , <b>2015</b> , 106, 142101	3.4	38
124	Carrier localization in In-rich InGaIn/GaN multiple quantum wells for green light-emitting diodes. <b>2015</b> , 5, 9373		72
123	InGaIn pn-junctions grown by PA-MBE: Material characterization and fabrication of nanocolumn electroluminescent devices. <b>2015</b> , 425, 393-397		7
122	Localization effect in green light emitting InGaIn/GaN multiple quantum wells with varying well thickness. <i>Journal of Alloys and Compounds</i> , <b>2015</b> , 625, 266-270	5.7	32

121	High luminous efficacy green light-emitting diodes with AlGaIn cap layer. <b>2016</b> , 24, 17868-73		60
120	Performance enhancement of blue light-emitting diodes with InGaIn/GaN multi-quantum wells grown on Si substrates by inserting thin AlGaIn interlayers. <b>2016</b> , 120, 113104		22
119	Light Emitting Diode Materials and Devices. <b>2016</b> , 273-311		
118	Investigation of amber light-emitting diodes based on InGaIn/AlN/AlGaIn quantum wells. <b>2016</b> , 55, 05FJ06		7
117	The microstructure of non-polar a-plane (11 $\bar{2}00$ ) InGaIn quantum wells. <b>2016</b> , 119, 175703		19
116	Green semipolar III-nitride light-emitting diodes grown by limited area epitaxy. <i>Applied Physics Letters</i> , <b>2016</b> , 109, 041107	3-4	7
115	Auger effect in yellow light emitters based on InGaIn/AlGaIn/GaN quantum wells. <b>2016</b> , 55, 05FG10		7
114	Temperature-dependent recombination coefficients in InGaIn light-emitting diodes: Hole localization, Auger processes, and the green gap. <i>Applied Physics Letters</i> , <b>2016</b> , 109, 161103	3-4	67
113	Highly stable and efficient green luminescent CdS colloidal nanocrystals. <b>2016</b> , 10, 026017		2
112	Investigation of NH <sub>3</sub> input partial pressure for N-polarity InGaIn growth on GaN substrates by tri-halide vapor phase epitaxy. <b>2016</b> , 55, 05FA01		5
111	Enhanced light output power of InGaIn-based amber LEDs by strain-compensating AlN/AlGaIn barriers. <b>2016</b> , 448, 105-108		32
110	Comparative study of (0001) and $\{11\bar{2}\}$ InGaIn based light emitting diodes. <b>2016</b> , 55, 05FJ10		7
109	Influences of Si-doped graded short-period superlattice on green InGaIn/GaN light-emitting diodes. <b>2016</b> , 24, 7743-51		19
108	Single-Layer Halide Perovskite Light-Emitting Diodes with Sub-Band Gap Turn-On Voltage and High Brightness. <b>2016</b> , 7, 4059-4066		144
107	Efficiency studies on semipolar GaInN/GaN quantum well structures. <b>2016</b> , 213, 3117-3121		5
106	Impact of Radiative and Nonradiative Recombination Processes on the Efficiency-Droop Phenomenon in In <sub>x</sub> Ga <sub>1-x</sub> N Single Quantum Wells Studied by Scanning Near-Field Optical Microscopy. <b>2016</b> , 6,		12
105	Decomposition of supercritical ammonia and modeling of supercritical ammonia-nitrogen-hydrogen solutions with applicability toward ammonothermal conditions. <b>2016</b> , 107, 17-30		22
104	Light-emitting diodes for solid-state lighting: searching room for improvements. <b>2016</b> ,		16

103	Optimized In composition and quantum well thickness for yellow-emitting (Ga,In)N/GaN multiple quantum wells. <b>2016</b> , 434, 25-29		4
102	Internal quantum efficiency and Auger recombination in green, yellow and red InGaN-based light emitters grown along the polar direction. <i>Superlattices and Microstructures</i> , <b>2017</b> , 103, 245-251	2.8	21
101	Ultraviolet, blue, and green InGaN-based light-emitting diodes functionalized with ZnO nanorods. <i>Journal of Alloys and Compounds</i> , <b>2017</b> , 708, 612-618	5.7	14
100	Effect of nanopillar sublayer embedded with SiO <sub>2</sub> on deep traps in green GaN/InGaN light emitting diodes. <b>2017</b> , 121, 045108		9
99	Effect of small flow hydrogen treatment at the upper well/barrier interface on the properties of InGaN/GaN multiple quantum wells. <i>Superlattices and Microstructures</i> , <b>2017</b> , 107, 293-298	2.8	4
98	Fabrication of InGaN/GaN MQW nano-LEDs by hydrogen-environment anisotropic thermal etching. <b>2017</b> , 214, 1600613		4
97	Green, Yellow, and Red LEDs. <b>2017</b> , 239-266		1
96	Development of Deep UV LEDs and Current Problems in Material and Device Technology. <b>2017</b> , 96, 45-83		16
95	Effects of Wavelength and Defect Density on the Efficiency of (In,Ga)N-Based Light-Emitting Diodes. <b>2017</b> , 7,		11
94	Flower-Like Internal Emission Distribution of LEDs with Monolithic Integration of InGaN-based Quantum Wells Emitting Narrow Blue, Green, and Red Spectra. <b>2017</b> , 7, 7164		5
93	Flower-like light distribution inside InGaN-based light-emitting diodes operated in spectral range from violet to red. <b>2017</b> ,		
92	Design and simulation to improve the structural efficiency of green light emission of GaN/InGaN/AlGaIn light emitting diode. <b>2017</b> , 10, 370-377		2
91	Strain compensation in InGaN-based multiple quantum wells using AlGaIn interlayers. <b>2017</b> , 7, 105312		28
90	Enhanced In incorporation in full InGaIn heterostructure grown on relaxed InGaIn pseudo-substrate. <i>Applied Physics Letters</i> , <b>2017</b> , 110, 262103	3.4	70
89	Carrier localization in InGaIn by composition fluctuations: implication to the green gap <i>Photonics Research</i> , <b>2017</b> , 5, A7	6	35
88	Diffusion-Driven Charge Transport in Light Emitting Devices. <i>Materials</i> , <b>2017</b> , 10,	3.5	8
87	Perspective: Toward efficient GaN-based red light emitting diodes using europium doping. <b>2018</b> , 123, 160901		66
86	Fundamental Limitations of Wide-Bandgap Semiconductors for Light-Emitting Diodes. <b>2018</b> , 3, 655-662		35

85	The influence of well thickness on the photoluminescence properties of blue-violet light emitting InGaN/GaN multiple quantum wells. <i>Superlattices and Microstructures</i> , <b>2018</b> , 113, 534-540	2.8	3
84	Influence of in doping in GaN barriers on luminescence properties of InGaN/GaN multiple quantum well LEDs. <i>Superlattices and Microstructures</i> , <b>2018</b> , 114, 32-36	2.8	5
83	Quantitative study of energy-transfer mechanism in Eu,O-codoped GaN by time-resolved photoluminescence spectroscopy. <b>2018</b> , 123, 161419		4
82	Optical properties of InGaN thin films in the entire composition range. <b>2018</b> , 123, 125101		27
81	Efficiency enhancement of InGaN amber MQWs using nanopillar structures. <i>Nanophotonics</i> , <b>2018</b> , 7, 317632	3.2	8
80	Effects of Introduction of InGaN Quantum Structures on Structural and Optical Properties of InGaN Nanocolumns. <i>Physica Status Solidi (B): Basic Research</i> , <b>2018</b> , 255, 1700481	1.3	1
79	Thickness Study of Er-Doped Magnesium Zinc Oxide Diode by Spray Pyrolysis. <i>Crystals</i> , <b>2018</b> , 8, 454	2.3	2
78	What is red? On the chromaticity of orange-red InGaN/GaN based LEDs. <b>2018</b> , 124, 183102		18
77	Integrating AlInN interlayers into InGaN/GaN multiple quantum wells for enhanced green emission. <i>Applied Physics Letters</i> , <b>2018</b> , 112, 201106	3.4	23
76	Development of high performance green c-plane III-nitride light-emitting diodes. <b>2018</b> , 26, 5591-5601		33
75	Performance enhancement of yellow InGaN-based multiple-quantum-well light-emitting diodes grown on Si substrates by optimizing the InGaN/GaN superlattice interlayer. <i>Optical Materials Express</i> , <b>2018</b> , 8, 1221	2.6	18
74	Influence of stress on the optical properties of double InGaN/GaN multiple quantum wells. <i>Optical Materials Express</i> , <b>2018</b> , 8, 1528	2.6	3
73	Effect of Carrier Localization on Recombination Processes and Efficiency of InGaN-Based LEDs Operating in the Green Gap <b>2018</b> , 8, 818		19
72	Evaluation of Light Extraction Efficiency of GaN-Based Nanorod Light-Emitting Diodes by Averaging over Source Positions and Polarizations. <i>Crystals</i> , <b>2018</b> , 8, 27	2.3	11
71	Study on the Coupling Mechanism of the Orthogonal Dipoles with Surface Plasmon in Green LED by Cathodoluminescence. <i>Nanomaterials</i> , <b>2018</b> , 8,	5.4	3
70	Infrared emitters using III-nitride semiconductors. <b>2018</b> , 587-617		3
69	III-Nitride Micro-LEDs for Efficient Emissive Displays. <b>2019</b> , 13, 1900141		54
68	Growth and characterization of In <sub>x</sub> Ga <sub>1-x</sub> N (0 < x < 1). <b>2019</b> , 520, 18-26		12

67	Analysis of efficiency curves in near-UV, blue, and green-emitting InGaN-based multiple quantum wells using rate equations of exciton recombination. <b>2019</b> , 58, SCCB02		5
66	High-luminous efficacy green light-emitting diodes with InGaN/GaN quasi-superlattice interlayer and Al-doped indium tin oxide film. <i>Journal of Alloys and Compounds</i> , <b>2019</b> , 794, 137-143	5-7	11
65	Tuning the Resonant Frequency of a Surface Plasmon by Double-Metallic Ag/Au Nanoparticles for High-Efficiency Green Light-Emitting Diodes. <b>2019</b> , 9, 305		5
64	Temperature dependence of the color rendering index of a phosphor-conversion white light-emitting diode. <b>2019</b> , 9, 015009		0
63	InGaN Platelets: Synthesis and Applications toward Green and Red Light-Emitting Diodes. <b>2019</b> , 19, 2832-2839	24	
62	Enhanced Device Performance of GaInN-Based Green Light-Emitting Diode with Sputtered AlN Buffer Layer. <b>2019</b> , 9, 788		10
61	Recombination rates in green-yellow InGaN-based multiple quantum wells with AlGaIn interlayers. <b>2019</b> , 126, 213106		7
60	On the Carrier Transport for InGaN/GaN Core-Shell Nanorod Green Light-Emitting Diodes. <b>2019</b> , 18, 176-182		5
59	The AlGaInP/AlGaAs Material System and Red/Yellow LED. <b>2019</b> , 171-202		1
58	Abnormal Stranski-Krastanov Mode Growth of Green InGaN Quantum Dots: Morphology, Optical Properties, and Applications in Light-Emitting Devices. <b>2019</b> , 11, 1228-1238		37
57	InGaN based tunable green light-emitting diodes using InAlN interlayer and strain compensated AlGaIn interlayer for better device performance. <b>2020</b> , 124, 105975		2
56	Direct detection of rare earth ion distributions in gallium nitride and its influence on growth morphology. <b>2020</b> , 127, 013102		4
55	Design and growth of GaN-based blue and green laser diodes. <i>Science China Materials</i> , <b>2020</b> , 63, 1348-1363	63	13
54	Improving the internal quantum efficiency of QD/QW hybrid structures by increasing the GaN barrier thickness.. <b>2020</b> , 10, 41443-41452		2
53	Increasing the Luminescence Efficiency of Long-Wavelength (In,Ga)N Quantum Well Structures by Electric Field Engineering Using an (Al,Ga)N Capping Layer. <b>2020</b> , 14,		1
52	Device quality templates of In <sub>x</sub> Ga <sub>1-x</sub> N (x Applied Physics Letters, <b>2020</b> , 117, 052103	3-4	6
51	Green gap in GaN-based light-emitting diodes: in perspective. <b>2020</b> , 1-18		5
50	A 3D simulation comparison of carrier transport in green and blue c-plane multi-quantum well nitride light emitting diodes. <b>2020</b> , 128, 235703		3

49	Observing relaxation in device quality InGaN templates by TEM techniques. <i>Applied Physics Letters</i> , <b>2020</b> , 116, 102104	3.4	12
48	Electronic properties of dilute-As InGaNAs alloys: A first-principles study. <b>2020</b> , 127, 015103		1
47	Photoluminescence properties of InGaN/GaN multiple quantum wells containing a gradually changing amount of indium in each InGaN well layer along the growth direction. <i>Journal of Luminescence</i> , <b>2020</b> , 223, 117225	3.8	6
46	High external quantum efficiency III-nitride micro-light-emitting diodes. <b>2021</b> , 106, 95-121		1
45	Performance Enhancement of InGaN/GaN Green QW LEDs with Different Interlayers and Doping in the Barriers. <b>2021</b> , 484-489		
44	Group-III-nitride and halide-perovskite semiconductor gain media for amplified spontaneous emission and lasing applications. <b>2021</b> , 54, 143001		7
43	Performance improvement of green QW LEDs, for the different doping in the barriers, using InAlN interlayer and strain compensated AlGaN interlayer at the InGaN/GaN interface. <b>2021</b> , 113, 110863		1
42	Strain-induced yellow to blue emission tailoring of axial InGaN/GaN quantum wells in GaN nanorods synthesized by nanoimprint lithography. <b>2021</b> , 11, 6754		2
41	Factors Affecting Surface Plasmon Coupling of Quantum Wells in Nitride-Based LEDs: A Review of the Recent Advances. <i>Nanomaterials</i> , <b>2021</b> , 11,	5.4	2
40	Influence of low-temperature GaN-Cap layer thickness on the InGaN/GaN multiple quantum well structure and its luminescence. <i>Optical Materials Express</i> , <b>2021</b> , 11, 1411	2.6	1
39	Effect of Graded-Indium-Content Superlattice on the Optical and Structural Properties of Yellow-Emitting InGaN/GaN Quantum Wells. <i>Materials</i> , <b>2021</b> , 14,	3.5	1
38	Step-type quantum wells with slightly varied InN composition for GaN-based yellow micro light-emitting diodes. <i>Applied Optics</i> , <b>2021</b> , 60, 3006-3012	1.7	0
37	Multi-colour light emission from InGaN nanowires monolithically grown on Si substrate by MBE. <i>Nanotechnology</i> , <b>2021</b> , 32,	3.4	3
36	Structure and luminescence properties of Eu <sup>3+</sup> and Dy <sup>3+</sup> implanted GaN films. <i>Superlattices and Microstructures</i> , <b>2021</b> , 156, 106974	2.8	1
35	Realization of III-Nitride c-Plane microLEDs Emitting from 470 to 645 nm on Semi-Relaxed Substrates Enabled by V-Defect-Free Base Layers. <i>Crystals</i> , <b>2021</b> , 11, 1168	2.3	3
34	. <i>IEEE Journal of Quantum Electronics</i> , <b>2021</b> , 57, 1-7	2	1
33	n-type GaN surface etched green light-emitting diode to reduce non-radiative recombination centers. <i>Applied Physics Letters</i> , <b>2021</b> , 118, 021102	3.4	7
32	Recent progress in nonpolar and semi-polar GaN light emitters on patterned Si substrates. <b>2018</b> ,		3

31	Improving carrier transport in AlGaIn deep-ultraviolet light-emitting diodes using a strip-in-a-barrier structure. <i>Applied Optics</i> , <b>2020</b> , 59, 5276-5281	1.7	11
30	Enhanced hole transport in AlGaIn deep ultraviolet light-emitting diodes using a double-sided step graded superlattice electron blocking layer. <i>Journal of the Optical Society of America B: Optical Physics</i> , <b>2020</b> , 37, 2564	1.7	5
29	Ultrapure and highly efficient green light emitting devices based on ligand-modified CsPbBr <sub>3</sub> quantum dots. <i>Photonics Research</i> , <b>2020</b> , 8, 1086	6	39
28	Efficient InGaIn-based yellow-light-emitting diodes. <i>Photonics Research</i> , <b>2019</b> , 7, 144	6	80
27	Semiconductor yellow light-emitting diodes. <i>Wuli Xuebao/Acta Physica Sinica</i> , <b>2019</b> , 68, 168503	0.6	3
26	III-Nitride Light-Emitting Devices. <i>Photonics</i> , <b>2021</b> , 8, 430	2.2	2
25	Shifting LED emission from blue to the green gap spectral range using In <sub>0.12</sub> Ga <sub>0.88</sub> N relaxed templates. <i>Superlattices and Microstructures</i> , <b>2021</b> , 160, 107065	2.8	2
24	Efficiency enhancement of III-nitride light-emitting diodes with strain-compensated thin-barrier InGaIn/AlIn/GaIn multiple quantum wells. <i>OSA Continuum</i> , <b>2019</b> , 2, 1207	1.4	1
23	Effect of InGaIn growth interruption on photoluminescence properties of an InGaIn-based multiple quantum well structure. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , <b>2020</b> , 119, 113982	3	3
22	Patterned sapphire substrates cause a wavelength shift of green InGaIn light-emitting diodes. <i>Optical Materials Express</i> , <b>2020</b> , 10, 2045	2.6	0
21	Near-Infrared Electroluminescence of AlGaIn Capped InGaIn Quantum Dots Formed by Controlled Growth on Photoelectrochemical Etched Quantum Dot Templates. <i>Photonics Research</i> ,	6	2
20	Investigation of Micromorphology and Carrier Recombination Dynamics for InGaIn/GaIn Multi-Quantum Dots Grown by Molecular Beam Epitaxy. <i>Crystals</i> , <b>2021</b> , 11, 1312	2.3	2
19	Enhanced P-Type GaIn Conductivity by Mg Delta Doped AlGaIn/GaIn Superlattice Structure. <i>Materials</i> , <b>2020</b> , 14,	3.5	4
18	Modulation and Refinement of In- re-Bonding of InGaIn Through in Post-Flow During a Refined Temper Fire Treatment Process. <i>IEEE Access</i> , <b>2020</b> , 8, 224433-224438	3.5	
17	InGaIn-Based microLED Devices Approaching 1% EQE with Red 609 nm Electroluminescence on Semi-Relaxed Substrates. <i>Crystals</i> , <b>2021</b> , 11, 1364	2.3	5
16	Temporally modulated energy shuffling in highly interconnected nanosystems. <i>Nanophotonics</i> , <b>2020</b> , 10, 851-876	6.3	3
15	Modeling of In <sub>0.17</sub> Ga <sub>0.83</sub> N/In <sub>x</sub> Ga <sub>1-x</sub> N/Al <sub>y</sub> Ga <sub>1-y</sub> N light emitting diode structure on ScAlMgO <sub>4</sub> (0001) substrate for high intensity red emission. <i>Semiconductor Physics, Quantum Electronics and Optoelectronics</i> , <b>2020</b> , 23, 408-414	0.4	
14	Greatly suppressed potential inhomogeneity and performance improvement of c-plane InGaIn green laser diodes. <i>Science China Materials</i> , 1	7.1	3



13	Optical Properties of GaN-Based Green Light-Emitting Diodes Influenced by Low-Temperature p-GaN Layer. <i>Nanomaterials</i> , <b>2021</b> , 11,	5.4	
12	Delta InN-InGaN Quantum Wells With AlGaIn Interlayers for Long Wavelength Emission. <i>IEEE Journal of Quantum Electronics</i> , <b>2022</b> , 58, 1-6	2	
11	Dilute-As InGaInAs/GaN Quantum Wells for High-Efficiency Red Emitters. <i>IEEE Journal of Quantum Electronics</i> , <b>2022</b> , 58, 1-6	2	0
10	Effect of low-temperature interlayer in active-region upon photoluminescence in multiple-quantum-well InGaIn/GaN. <i>Journal of Luminescence</i> , <b>2022</b> , 244, 118741	3.8	0
9	Photoluminescence Study of Carrier Localization and Recombination in Nearly Strain-Balanced Nonpolar InGaIn/AlGaIn Quantum Wells. <i>Physica Status Solidi (B): Basic Research</i> , 2100569	1.3	
8	Structural and emission improvement of cyan-emitting InGaIn quantum wells by introducing a large substrate misorientation angle. <i>Optical Materials Express</i> , <b>2022</b> , 12, 119	2.6	1
7	Reduction of V-pit density and depth in InGaIn semibulk templates and improved LED performance with insertion of high temperature semibulk layers. <i>Semiconductor Science and Technology</i> , <b>2022</b> , 37, 075003	1.8	
6	Cubic In <sub>x</sub> Ga <sub>1-x</sub> N/GaN quantum wells grown by Migration Enhanced Epitaxy (MEE) and conventional Molecular Beam Epitaxy (MBE). <i>Journal of Alloys and Compounds</i> , <b>2022</b> , 165994	5.7	1
5	Investigation into the stability condition of correlated color temperature of white illumination sources based on trichromatic light-emitting diodes. <b>2023</b> , 76, 102358		0
4	Recombination Rate Analysis of InGaIn-Based Red-Emitting Light-Emitting Diodes. <b>2023</b> , 59, 1-9		0
3	The effect of ammonia partial pressure on the growth of semipolar (1102) InGaIn/GaN MQWs and LED structures. <b>2023</b> , 291, 116368		0
2	An Ultrahigh Efficiency Excitonic Micro-LED. <b>2023</b> , 23, 1680-1687		1
1	Application of nano-patterned InGaIn fabricated by self-assembled Ni nano-masks in green InGaIn/GaN multiple quantum wells. <b>2023</b> , 44, 042801		0